MMSTA92

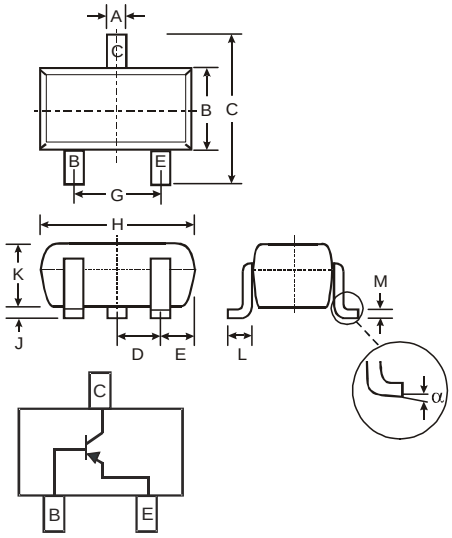
PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (MMSTA42)
- Ideal for Low Power Amplification and Switching
- **Lead Free/RoHS Compliant (Note 2)**
- **"Green" Device (Notes 3 and 4)**

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 4. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)



SOT-323		
Dim	**Min**	**Max**
A	0.25	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.18
α	0°	8°
All Dimensions in mm		

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-300	V
Collector-Emitter Voltage	V_{CEO}	-300	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current (Note 1)	I_C	-100	mA
Power Dissipation (Note 1)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300	—	V	I_C = -100μA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300	—	V	I_C = -1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0	—	V	I_E = -100μA, I_C = 0
Collector Cutoff Current	I_{CBO}	—	-250	nA	V_{CB} = -200V, I_E = 0
Collector Cutoff Current	I_{EBO}	—	-100	nA	V_{CE} = -3.0V, I_C = 0
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h_{FE}	25 40 25	—	—	I_C = -1.0mA, V_{CE} = -10V I_C = -10mA, V_{CE} = -10V I_C = -30mA, V_{CE} = -10V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.5	V	I_C = -20mA, I_B = -2.0mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	-0.9	V	I_C = -20mA, I_B = -2.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{cb}	—	6.0	pF	V_{CB} = -20V, f = 1.0MHz, I_E = 0
Current Gain-Bandwidth Product	f_T	50	—	MHz	V_{CE} = -20V, I_C = -10mA, f = 100MHz

Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
2. No purposefully added lead.
3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
4. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.
5. Short duration pulse test used to minimize self-heating effect.

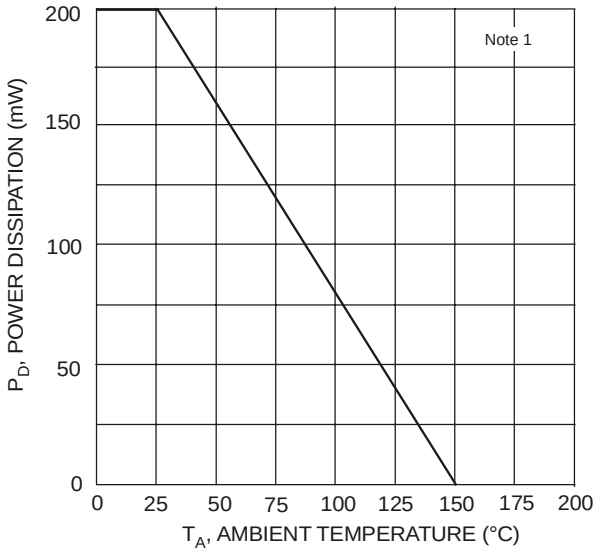


Fig. 1, Max Power Dissipation vs. Ambient Temperature

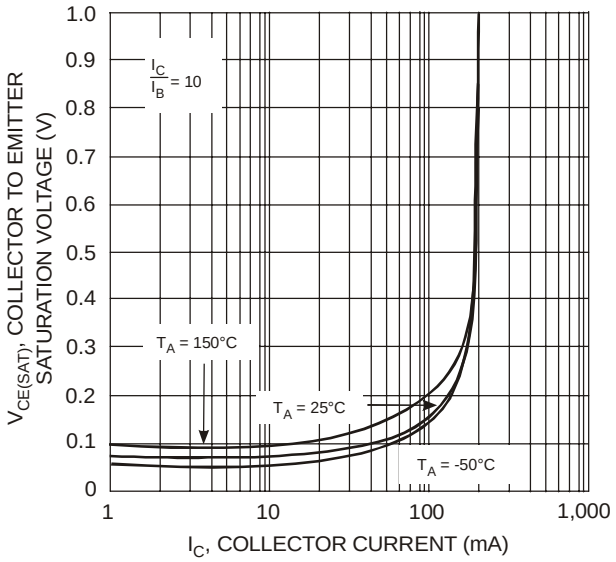


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

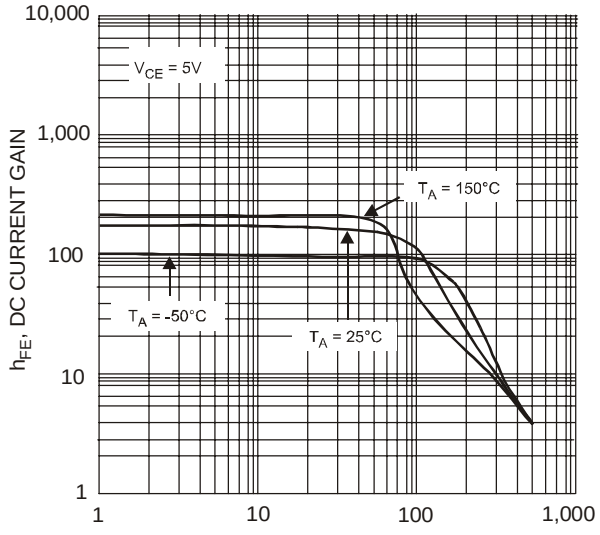


Fig. 3, DC Current Gain vs. Collector Current

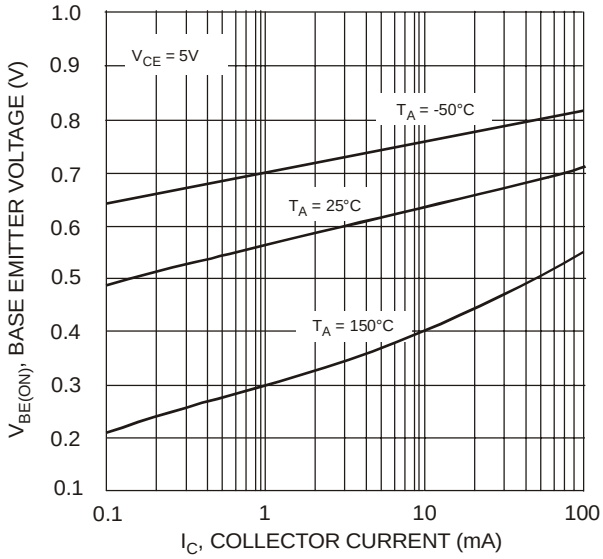


Fig. 4, Base Emitter Voltage vs. Collector Current

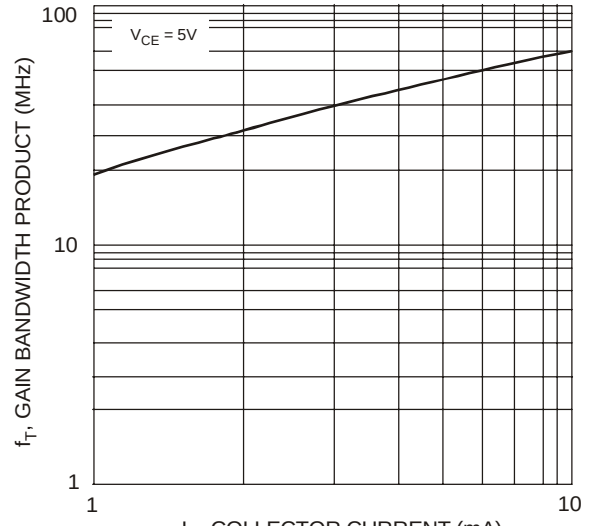


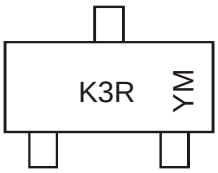
Fig. 5, Gain Bandwidth Product vs. Collector Current

Ordering Information (Note 4 and 6)

Device	Packaging	Shipping
MMSTA92-7-F	SOT-323	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



K3R = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: N = 2002
M = Month ex: 9 = September

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	M	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D